

Features and Applications

- Low ON-state resistance.
- high-speed switching.
- 4V drive.

TENTATIVE

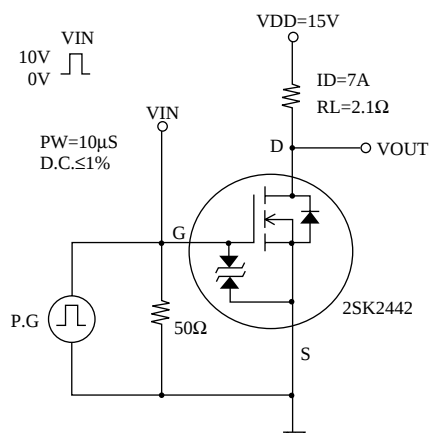
Absolute Maximum Ratings / Ta=25°C

			unit
Drain to Source Voltage	VDSS	30	V
Gate to Source Voltage	VGSS	±20	V
Drain Current (D.C)	ID	7	A
Drain Current (Pulse)	IDP	PW≤10μS, dutycycle≤1%	A
Allowable power Dissipation	PD	Mounted on ceramic board (1000mm ² ×0.8mm)	2.0 W
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	-55 to +150	°C

Electrical Characteristics / Ta=25°C

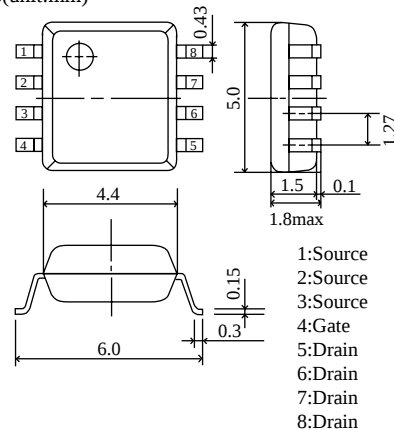
			min	typ	max	unit
Drain to Source Breakdown Voltage	V(BR)DSS	ID=1mA , VGS=0	30			V
Zero Gate Voltage Drain Current	IDSS	VDS=30V , VGS=0			100	μA
Gate to Source Leakage Current	IGSS	VGS=±16V , VDS=0			±10	μA
Cutoff Voltage	VGS(off)	VDS=10V , ID=1mA	1.0		2.5	V
Forward Transfer Admittance	yfs	VDS=10V , ID=7A	8	12		S
Static Drain to Source	RDS(on)1	ID=7A , VGS=10V		24	29	mΩ
On State Resistance	RDS(on)2	ID=4A , VGS=4V		34	48	mΩ
Input Capacitance	Ciss	VDS=10V , f=1MHz		1000		pF
Output Capacitance	Coss	VDS=10V , f=1MHz		780		pF
Reverse Transfer Capacitance	Crss	VDS=10V , f=1MHz		220		pF
Turn-ON Delay Time	td(on)	See Specified Test Circuit .		15		ns
Rise Time	tr	"		220		ns
Turn-off Delay Time	td(off)	"		190		ns
Fall Time	tf	"		230		ns
Diode Forward Voltage	VSD	IS = 7A , VGS = 0		1.0	1.2	V

Switching Time Test Circuit



Case Outline (unit:mm)

SOP8(unit:mm)



Specifications and information herein are subject to change without notice.

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